TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

# 2SK3670

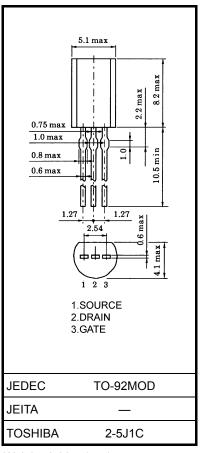
### Chopper Regulator and DC-DC Converter Applications

Unit: mm

- 2.5V-Gate Drive
- Low drain-source ON resistance: RDS (ON) =  $1.0 \Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 2.1 \text{ S (typ.)}$
- Low leakage current:  $IDSS = 100 \mu A (max) (VDS = 150 V)$
- Enhancement mode:  $V_{th} = 0.5 \sim 1.3 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 200 \,\mu\text{ A})$

### Absolute Maximum Ratings (Ta = 25°C)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			$V_{DSS}$	150	V
Drain-gate voltage (R <sub>GS</sub> = 20 kΩ)			$V_{DGR}$	150	V
Gate-source voltage			V <sub>GSS</sub>	±12	V
Drain current	DC	(Note 1)	I <sub>D</sub>	0.67	
	Pulse(t≦5s) (Note 1)		I <sub>DP</sub>	1	А
	Pulse	(Note 1)	I <sub>DP</sub>	3	
Drain power dissipation			$P_{D}$	0.9	W
Single pulse avalanche energy (Note 2)			E <sub>AS</sub>	41	m J
Avalanche current			I <sub>AR</sub>	0.67	Α
Repetitive avalanche energy (Note 3)			E <sub>AS</sub>	0.09	m J
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature range			T <sub>stg</sub>	-55~150	°C



Weight: 0.36 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

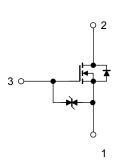
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	138	°C/W



Note 2:  $V_{DS}$  = 50V,  $T_{ch}$  = 25°C(initial), L = 135mH,  $I_{AR}$  = 0.67A,  $R_G$  = 25  $\Omega$ 

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.





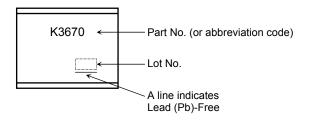
## Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition		Тур.	Max	Unit	
Gate leakage current		I <sub>GSS</sub>	V <sub>GS</sub> = ±9.6 V, V <sub>DS</sub> = 0 V		_	±10	μΑ	
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V		_	100	μA	
Drain-source br	eakdown voltage	V <sub>(BR) DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V		_	_	V	
Gate threshold v	oltage	$V_{th}$	V <sub>DS</sub> = 10 V, I <sub>D</sub> =200 μ A		_	1.3	V	
Drain-source ON resistance		R <sub>DS (ON)</sub>	V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 0.5 A	_	1.1	2	Ω	
			V <sub>GS</sub> = 4 V, I <sub>D</sub> = 0.5 A		1.0	1.7		
Forward transfer admittance		Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.5 A		2.1	_	S	
Input capacitance		C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz		230	_	pF	
Reverse transfer capacitance		C <sub>rss</sub>			14	_		
Output capacitance		C <sub>oss</sub>			50	_		
Switching time	Rise time	t <sub>r</sub>	$V_{QS}$ $V_{QS}$ $V_{DD}$ $= 0.5$ A OUT $V_{QS}$ $V_{DD}$ $= 75$ V Duty $\leq$ 1%, $V_{W}$ $= 10$ $\mu s$	_	16	_	ns	
	Turn-on time	t <sub>on</sub>		_	40	_		
	Fall time	t <sub>f</sub>		l	23			
	Turn-off time	t <sub>off</sub>		_	95	_		
Total gate charge (gate-source plus gate-drain)		Qg	V <sub>DD</sub> ≈ 120 V, V <sub>GS</sub> = 5 V, I <sub>D</sub> = 1 A		4.6	_		
Gate-source charge		$Q_{gs}$			2.9	_	nC	
Gate-drain ("miller") Charge		Q <sub>gd</sub>			1.7			

### **Source-Drain Ratings and Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	_	_	_	0.67	Α
Pulse drain reverse current (t=5s) (Note 1)	I <sub>DRP</sub>	_	_	_	1	Α
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	_	_	_	3	Α
Forward voltage (diode)	V <sub>DSF</sub>	I <sub>DR</sub> = 0.5 A, V <sub>GS</sub> = 0 V	_	_	-1.5	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 1A, V <sub>GS</sub> = 0V	_	95	_	ns
Reverse recovery charge	Q <sub>rr</sub>	$dI_{DR} / dt = 50A / \mu s$	_	110	_	nC

## Marking



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